

# Schottky barrier diode

## RB411D

### ●Applications

Low power rectification  
For switching power supply

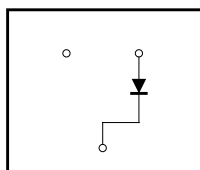
### ●Features

- 1) Small surface mounting type. (SMD3)
- 2) Low  $V_F$ . ( $V_F=0.43V$  Typ. at 0.5A)
- 3) High reliability.

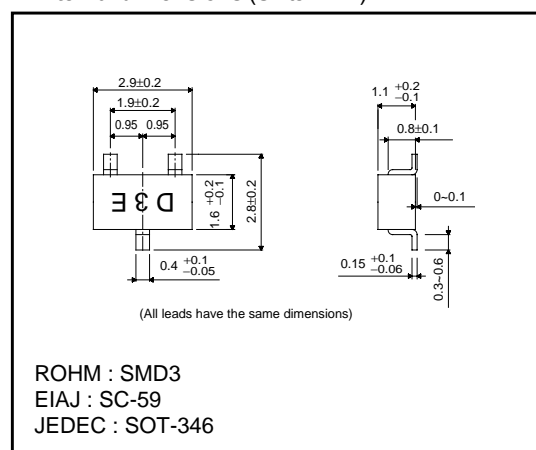
### ●Construction

Silicon epitaxial planar

### ●Circuit



### ●External dimensions (Units : mm)



### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	20	V
Mean rectifying current	$I_o$	0.5	A
Peak forward surge current *	$I_{FSM}$	3	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40~+125	$^\circ\text{C}$

\* 60Hz for 1  $\mu\text{s}$

### ●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	-	-	0.3	V	$I_F=10\text{mA}$
Forward voltage	$V_{F2}$	-	-	0.5	V	$I_F=500\text{mA}$
Reverse current	$I_R$	-	-	30	$\mu\text{A}$	$V_R=10\text{V}$
Capacitance between terminals	$C_T$	-	20	-	pF	$V_R=10\text{V}, f=1\text{MHz}$

Note) sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

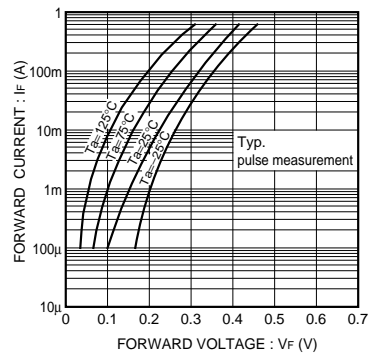


Fig. 1 Forward characteristics

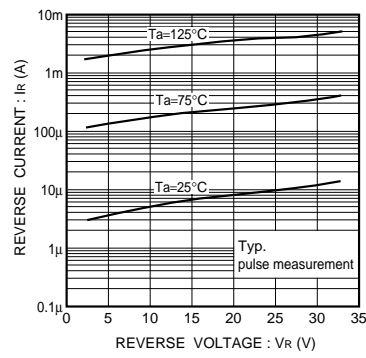


Fig. 2 Reverse characteristics

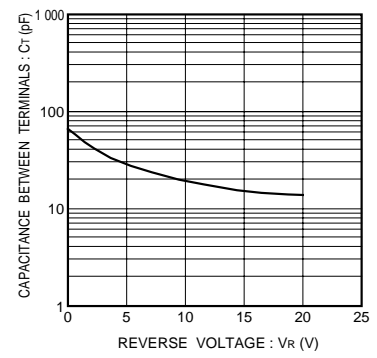


Fig. 3 Capacitance between terminals characteristic